

INFORMATION DISCLOSURE CITATION

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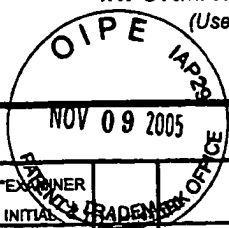
ATTY DOCKET NO.
2002US304

SERIAL NO.
10/042,878

Mark O. NEISSER et al.

FILING
January 9, 2002

GROUP
1756



U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ny	4,491,628	1/1/1985	Ito et al.	430	176	
	4,521,274	6/4/1985	Reichmanis et al.	216	47	
	5,069,997	5/16/1989	Schwalm et al.	430	270.1	
	5,350,660	9/27/1994	Urano et al.	430	170	
	5,354,643	10/11/1994	Cabrera et al.	430	270.1	
	5,389,491	2/14/1995	Tani et al.	430	170	
	5,419,991	5/30/1995	Segawa	430	20	
	5,581,730	12/3/1996	Silla	711	144	
	5,585,219	12/17/1996	Kaimoto et al.	430	270.1	
ny	5,693,691	12/2/1997	Flaim et al.	523	436	
ny	5,716,756	2/10/1998	Pawlowski et al.	430	270.1	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
ny	JP 5-107770	4/30/1993	JAPAN	—	—	✓	
ny	JP 7-159997	6/23/1995	JAPAN	—	—	✓	
ny	JP 7-181687	7/21/1995	JAPAN	—	—	✓	
ny	JP 8-286384	11/1/1996	JAPAN	—	—	✓	
ny	JP 9-205057	8/5/1997	JAPAN	—	—	✓	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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Michael W. ...

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h	5,994,006	11/30/1999	Nishi	4130	22	
h	6,110,641	8/29/2000	Trefonas, III et al.	4130	270.1	
	6,110,653	8/29/2000	Holmes et al.	4130	325	
	6,316,165	11/13/2001	Pavelchek et al.	4130	311	
	6,319,651	11/20/2001	Holmes et al.	4130	270.1	
	6,322,948	11/27/2001	Jung et al.	4130	270.1	
	6,329,117	12/11/2001	Padmanaban et al.	4130	270.1	
	2003/0104322	6/5/2003	Yamashita et al.	4130	331	
	2003/0129531	7/10/2003	Oberlander et al.	4130	271.1	
	2003/0215736	11/20/2003	Oberlander et al.	4130	270.1	
h	2004/0013971	1/22/2004	Berger et al.	4130	270.1	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
h	EP 0 794 458	9/10/1997	EUROPE				
h	EP 0 905 565	3/31/1999	EUROPE				
h	GB 2 320 718	7/1/1998	UNITED KINGDOM				
h	GB 2 354 763	4/4/2001	UNITED KINGDOM				
h	WO 97/33198	9/12/1997	WIPO				

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WJ	5,286,867	2/15/1994	Lohaus et al.	546	249	
WJ	5,338,641	8/16/1994	Pawlowski et al.	430	145	
WJ	5,340,682	8/23/1994	Pawlowski et al.	430	145	

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
WJ	JP 2000-171604	6/23/2000	JAPAN				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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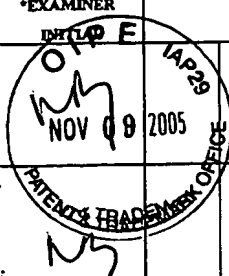
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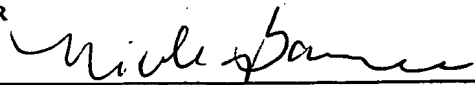
DATE CONSIDERED

1/20/06

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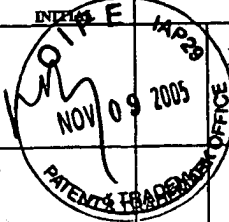
INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>		Docket Number (Optional) 2004US304	Application Number 10/042,878
		Applicant(s) Mark O. NEISSER et al.	
		Filing Date January 9, 2002	Group Art Unit 1756


*EXAMINER	OTHER DOCUMENTS	(Including Author, Title, Date, Pertinent Pages, Etc.)
	INITIAL	Bather et al., "Titanium Nitride Oxide (TiNxOy) as a Barrier Between Chromium-Silicon-Oxygen (Cr-Si-O)) and Aluminium Thin Films", Thin Solid Films Vol. 200, pages 93 - 116 (1991).
	NY	Cho et al., "Negative tone 193 nm resists", SPIE Vol. 3999, pages 62 - 73 (2000).
	NY	Choi et al., "Design and Synthesis of New Photoresist Materials for ArF Lithography", SPIE Vol. 3999, pages 54 - 61 (2000).
	NY	Choi et al., "Improved Lithographic Performance of 193nm-Photoresists Based on Cycloolefin / Maleic Anhydride Copolymer by Employing Mixed PAGs", SPIE Vol. 4345, pages 94 - 105 (2001).
	NY	Czech et al., "Reduction of Linewidth Variation for the Gate Conductor Level by Lithography Based on a New Antireflective Layer", Microelectronic Engineering Vol. 21, pages 51 - 56 (1993).
	NY	Fu et al., "Negative-tone Cycloolefin Photoresist for 193 nm Lithography", SPIE Vol. 4345, pages 751 - 760 (2001).
	NY	Houlihan et al., "Chemically Amplified Resists: The Chemistry and Lithographic Characteristics of Nitrobenzyl Benzenesulfonate Derivatives", Journal of Photopolymer Science and Technology Vol. 3, No. 3, pages 259 - 273 (1990).
	NY	Ito, "Chemically Amplified Resists: Past, Present, and Future", SPIE Vol. 3678, pages 2 - 12 (March 1999).
	NY	Iwasa et al., "Novel negative photoresist based on polar alicyclic polymers for ArF excimer laser lithography", SPIE Vol. 3333, pages 417 - 424 ().
	NY	Naito et al., "Negative-type chemically amplified resists for ArF excimer laser lithography", SPIE Vol. 3333, pages 503 - 511 ().
NY	Nölscher et al., "High contract single layer resists and antireflection layers - an alternative to multilayer resist techniques", SPIE Vol. 1086, pages 242 - 250 (1989).	
NY	Richter et al., "Negative Tone Resist for Phase-Shifting Mask Technology: A Progress Report", SPIE Vol. 3999, pages 91 - 101 (2000).	

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		Applicant(s) Mark O. NEISSER et a.	
		Filing Date January 9, 2002	Group Art Unit 1756

*EXAMINER	OTHER DOCUMENTS	(Including Author, Title, Date, Pertinent Pages, Etc.)
		Rushkin et al., "New Polymers for 193 nm Single Layer Resists Based on Substituted Cycloolefins/Maleic Anhydride Resins", SPIE Vol. 3678, pages 44 - 50 (March 1999).
		Schlegel et al., "Studies on the Acid Formation and Deprotection Reaction by Sovel Sulfonates in a Chemical Positive Photoresist", Journal of Photopolymer Science and Technology Vol. 3, No. 3, pages 281 - 287 (1990).
		Shida et al., "193-nm Single Layer Resists Based on Advanced Materials", SPIE Vol. 4345, pages 87 - 93 (2001).
		Shirai et al., "Photochemistry of Imino Sulfonate Compounds and Their Application to Chemically Amplified Resists", Journal of Photopolymer Science and Technology Vol. 3, No. 3, pages 301 - 304 (1990).
		Yamaoka et al., "Photochemical Dissociation of p-Nitrobenzyl Aromatic Sulfonate and Its Application to Chemical Amplification Resists", Journal of Photopolymer Science and Technology Vol. 3, No. 3, pages 275 - 280 (1990).
		Yokoyama et al., "ArF Negative Resist System Using Androsterone Structure with 6-Hydroxy Acid for 100-nm Phase-Shifting Lithography", SPIE Vol. 4345, pages 58 - 66 (2001).
		Yokoyama et al., "Effect of Comonomer Structure on Dissolution Characteristics: ArF Negative Resist System Using Androsterone Derivative with 7-Hydroxy Acid", Journal of Photopolymer Science and Technology Vol. 14, No. 3, pages 393 - 400 (2001).
		Copy of Official Action (and English translation thereof) for JP Application No. Hei-10-186575.
		English Language abstract of 2000-171604.

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